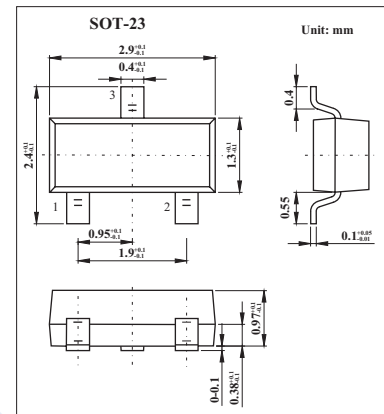


Schottky Barrier Diode

KB411D(RB411D)

■ Features

- Small surface mounting type
- Low VF. (VF=0.43V Typ. at 0.5A)
- High reliability.
- Silicon epitaxial planar



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Reverse voltage	V _{RM}	40	V
DC Reverse voltage	V _R	20	V
Mean rectifying current	I _o	0.5	A
Forward current surge peak	I _{FSM}	3	A
Junction temperature	T _j	125	°C
Storage temperature	T _{stg}	-40 to +125	°C

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Forward voltage	V _{F1}	I _F =500mA			0.50	V
	V _{F2}	I _F =10mA			0.30	V
Reverse current	I _{R1}	V _R =10V			30	μA
Capacitance between terminal	C _T	V _R =10V, f=1MHz		20		pF

■ Marking

Marking	D3E
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